

2nd Generation thinQ!TM SiC Schottky Diode

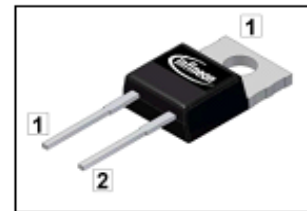
Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery/ No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Breakdown voltage tested at 5mA²⁾

Product Summary

V_{DC}	600	V
Q_c	8	nC
I_F	4	A

PG-TO220-2



thinQ! 2G Diode specially designed for fast switching applications like:

- CCM PFC
- Motor Drives

Type	Package	Marking	Pin 1	Pin 2
IDH04S60C	PG-TO220-2	D04S60C	C	A

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	I_F	$T_C < 140\text{ °C}$	4	A
RMS forward current	$I_{F,RMS}$	$f=50\text{ Hz}$	5.6	
reasonably be expected to cause the failure of that life-support , automotive, aviation and	$I_{F,SM}$	$T_C=25\text{ °C}$, $t_p=10\text{ ms}$	32	
Life support systems are intended to b	$I_{F,RM}$	$T_j=150\text{ °C}$, $T_C=100\text{ °C}$, $D=0.1$	18	
and sustain and/or protect human life.	$I_{F,max}$	$T_C=25\text{ °C}$, $t_p=10\text{ }\mu\text{s}$	132	
of the user or other persons may be e	V_{RRM}		600	V
Diode dv/dt ruggedness	dv/dt	$V_R = 0\dots 480\text{V}$	50	V/ns
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	42	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 175	°C
Mounting torque		M3 and M3.5 screws	60	Mcm
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6mm (0.063 in.) from case for 10s	260	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	3.6	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified
Static characteristics

DC blocking voltage	V_{DC}	$I_R=0.05\text{ mA}$	600	-	-	V
Diode forward voltage	V_F	$I_F=4\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	1.7	1.9	
		$I_F=4\text{ A}, T_j=150\text{ }^\circ\text{C}$	-	2	2.4	
Reverse current	I_R	$V_R=600\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	0.5	50	μA
		$V_R=600\text{ V}, T_j=150\text{ }^\circ\text{C}$	-	2	500	

Infineon Technologies components may be used in life-support devices or systems
and/or automotive, aviation and aerospace applications or systems only with

reasonably be expected to cause the failure of an	Q_c	$V_R=400\text{ V}, I_F \leq I_{F,max},$ $di_F/dt=200\text{ A}/\mu\text{s},$ $T_j=150\text{ }^\circ\text{C}$	-	8	-	nC
aerospace device or system or to affect the safety of						
Life support systems are intended to be used in	t_c		-	-	<10	ns
and sustain and/or protect human life.	C	$V_R=1\text{ V}, f=\text{MHz}$	-	130	-	pF
of the user or other persons may be endangered.			$V_R=600\text{ V}, f=1\text{ MHz}$	-	20	

¹⁾ J-STD20 and JESD22

²⁾ All devices tested under avalanche conditions, for a time period of 5ms, at 5mA.

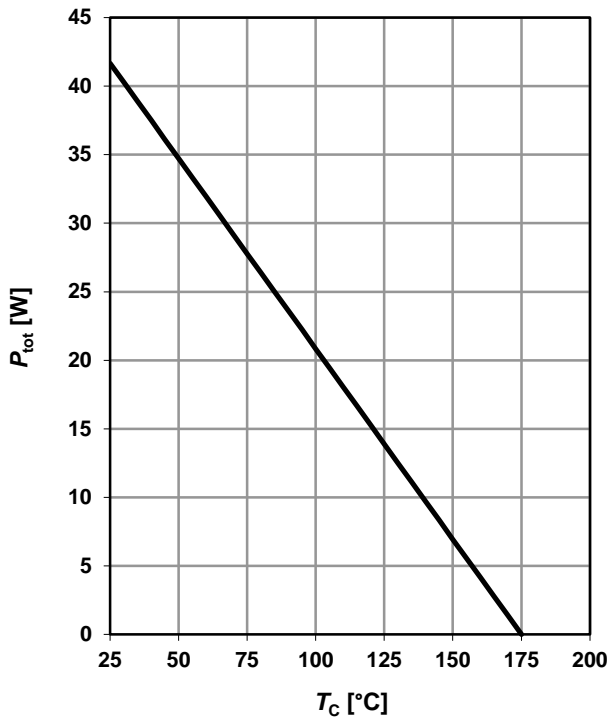
³⁾ t_c is the time constant for the capacitive displacement current waveform (independent from T_j, I_{LOAD} and di/dt), different from t_{rr} , which is dependent on $T_j, I_{LOAD}, di/dt$. No reverse recovery time constant t_{rr} due to absence of minority carrier injection.

⁴⁾ Only capacitive charge occurring, guaranteed by design.

1 Power dissipation

$P_{tot}=f(T_C)$

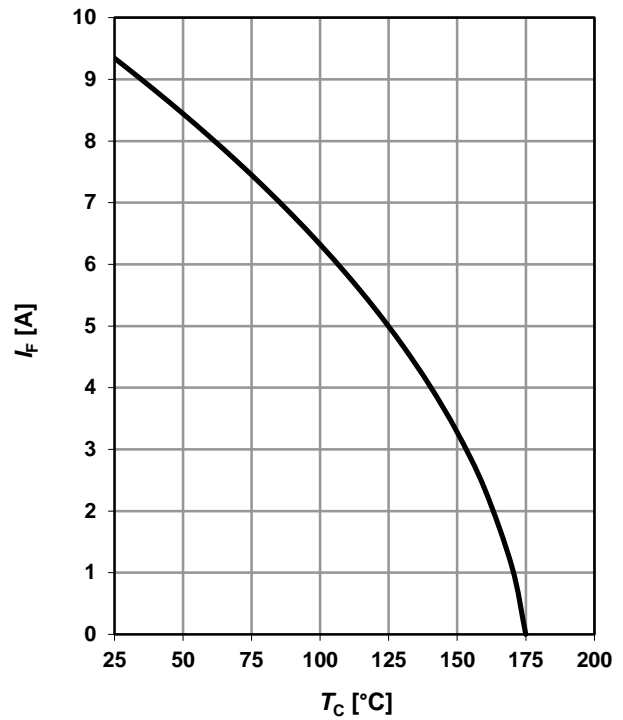
parameter: $R_{thJC(max)}$



2 Diode forward current

$I_F=f(T_C); T_j \leq 175\text{ °C}$

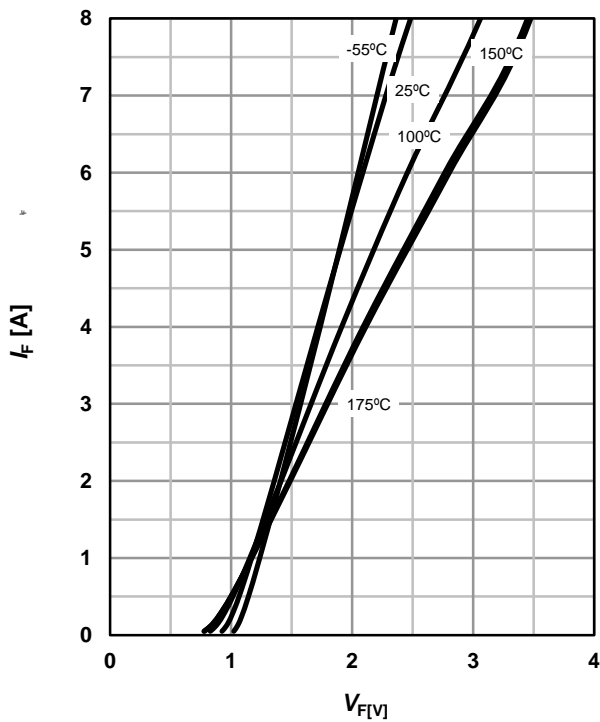
parameter: $R_{thJC(max)}$; $V_{F(max)}$



3 Typ. forward characteristic

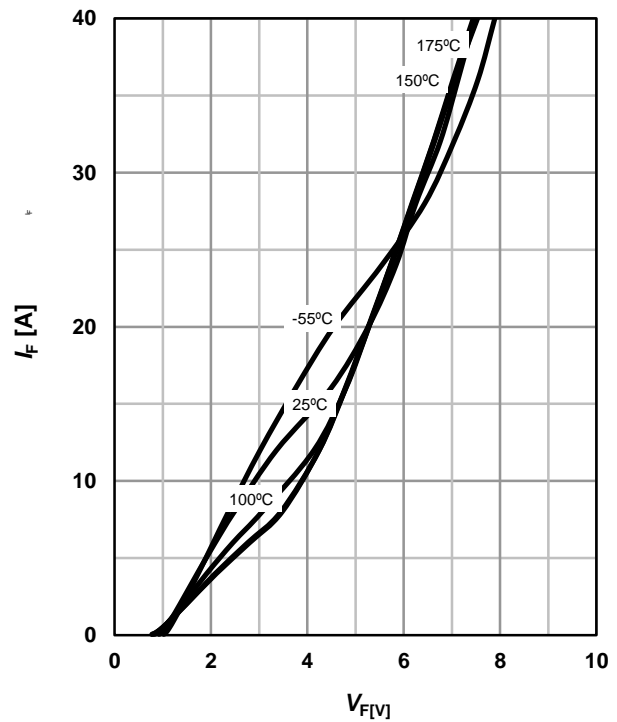
$I_F=f(V_F); t_p=400\text{ }\mu\text{s}$

parameter: T_j



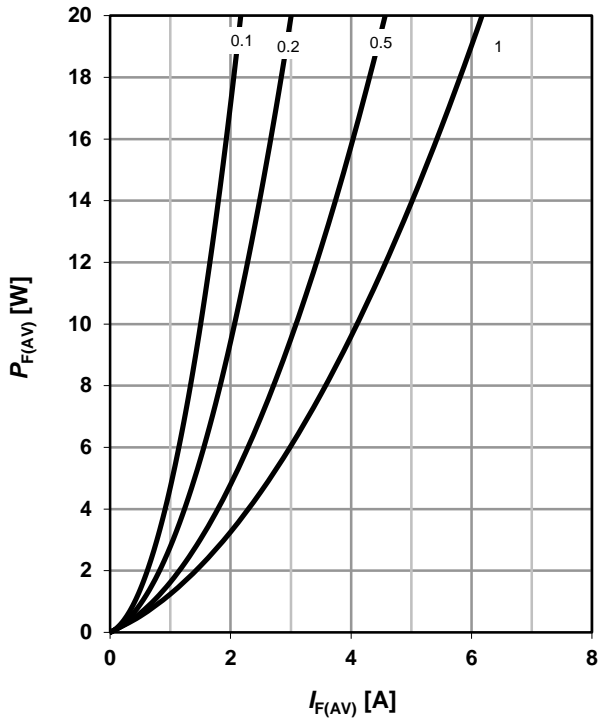
4 Typ. forward characteristic in surge current mode

$I_F=f(V_F); t_p=400\text{ }\mu\text{s};$ parameter: T_j



5 Typ. forward power dissipation vs. average forward current

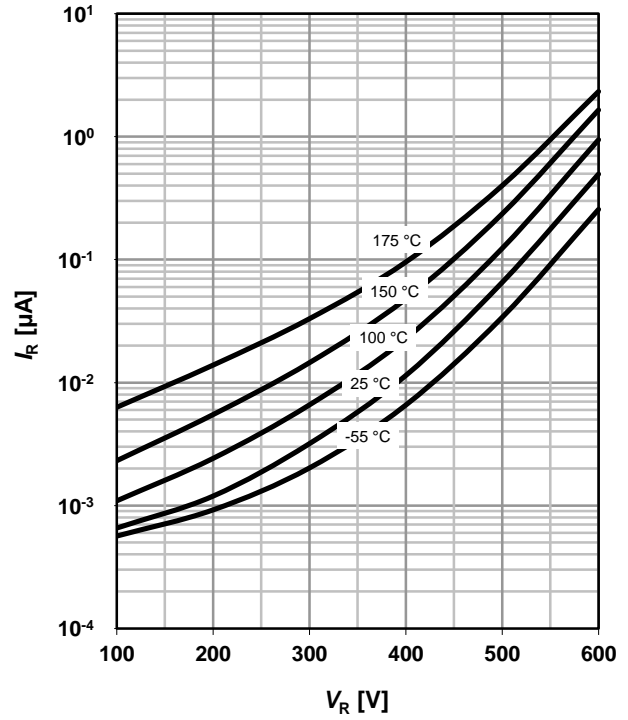
$P_{F,AV}=f(I_F)$, $T_C=100\text{ °C}$, parameter: $D=t_p/T$



6 Typ. reverse current vs. reverse voltage

$I_R=f(V_R)$

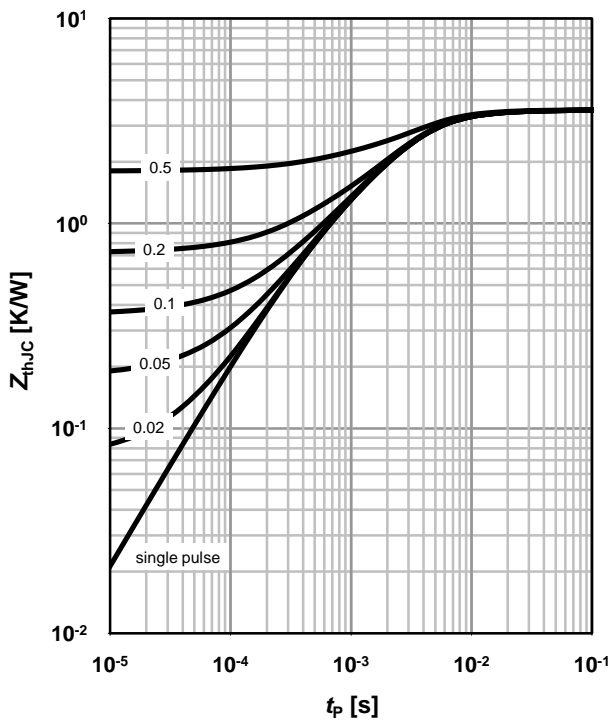
parameter: T_j



7 Transient thermal impedance

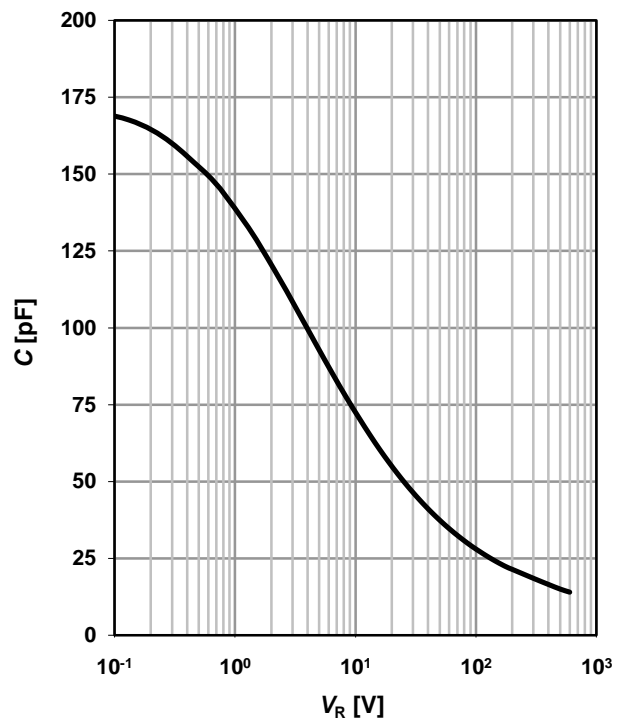
$Z_{thJC}=f(t_p)$

parameter: $D=t_p/T$



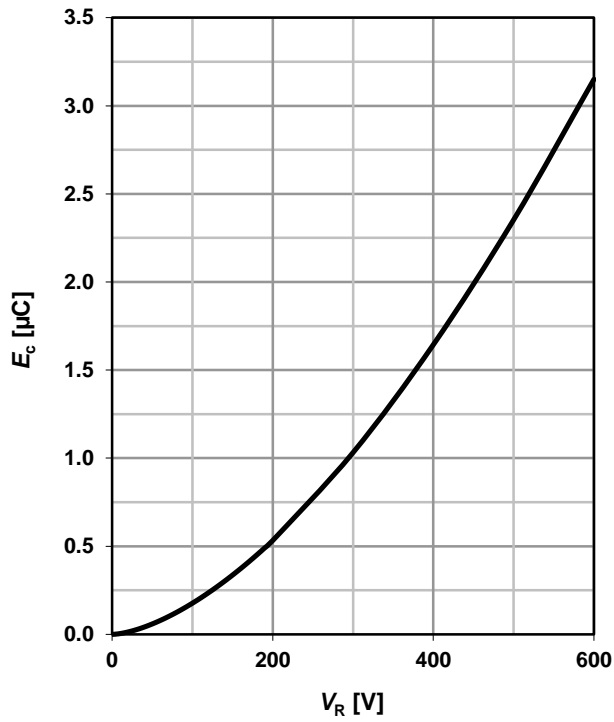
8 Typ. capacitance vs. reverse voltage

$C=f(V_R)$; $T_C=25\text{ °C}$, $f=1\text{ MHz}$



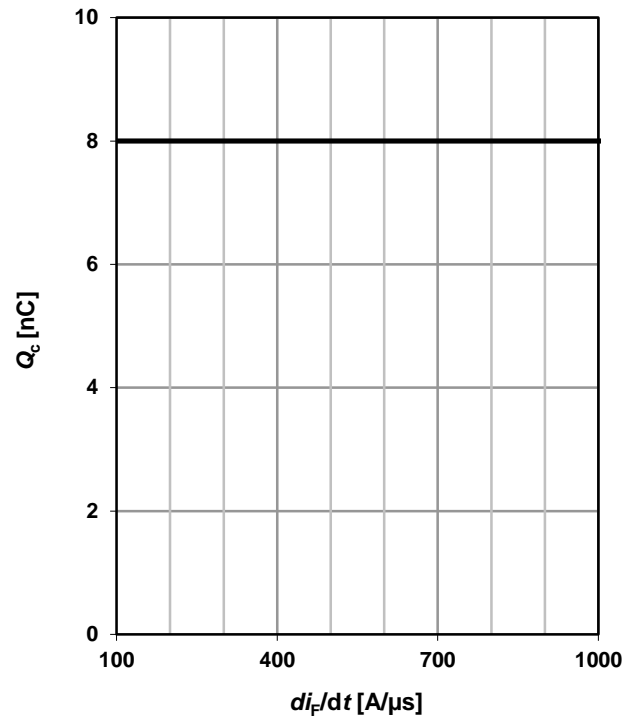
9 Typ. C stored energy

$$E_C = f(V_R)$$

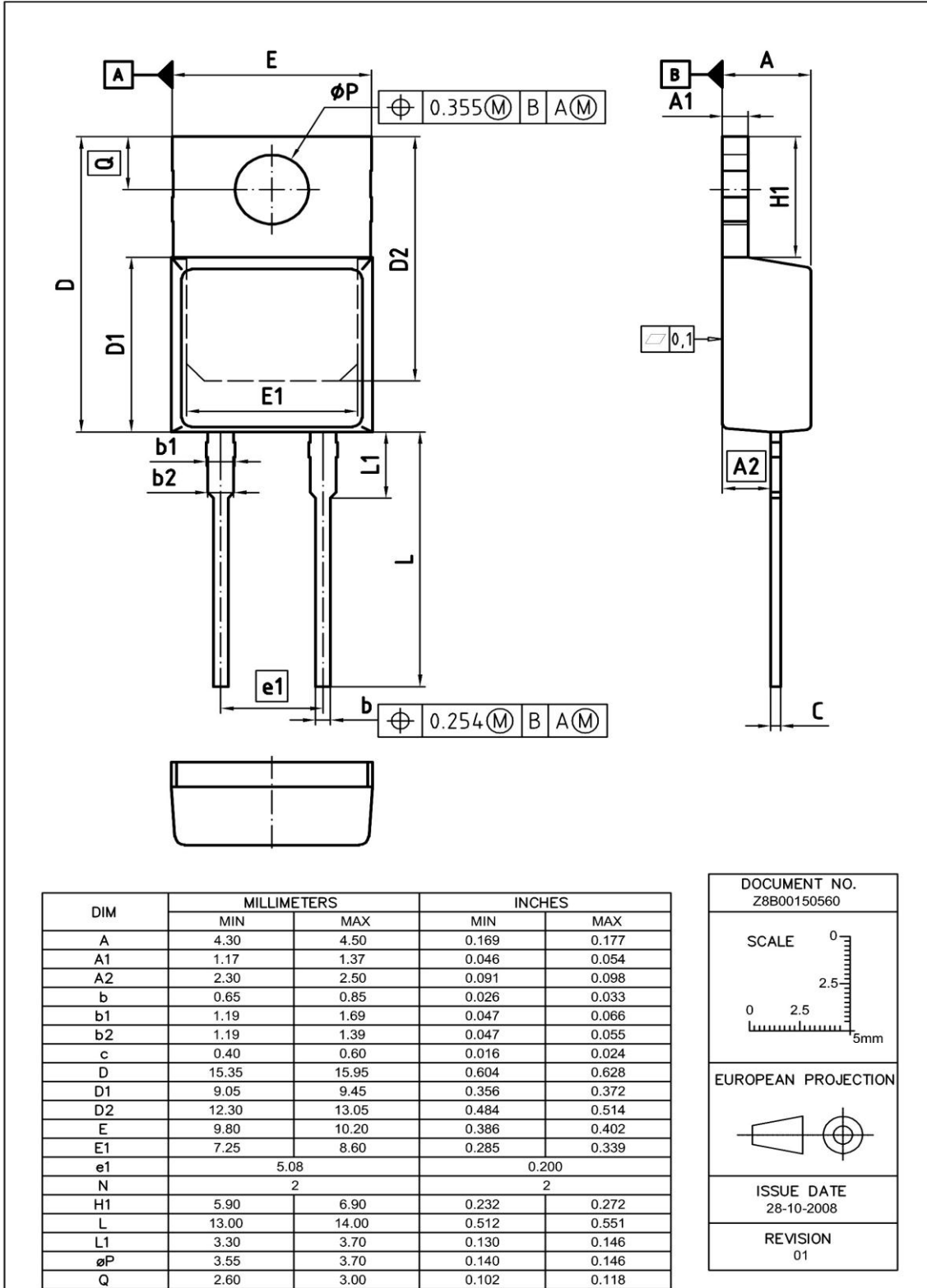


10 Typ. capacitance charge vs. current slope

$$Q_C = f(di_F/dt)^4; T_j = 150 \text{ °C}; I_F \leq I_{F,max}$$



PG-T0220-2: Outline



Dimensions in mm/inches

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Infineon Technologies AG
81726 Munich, Germany
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